

L Number	Hits	Search Text	DB	Time stamp
3	8455	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:32
4	289	((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:38
5	30	((((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and (((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:40
6	0	chia-der-chang-hsin-chu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:41
7	0	hsin-chu-chia-der-chang.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:42
8	0	chia-der-chang.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:42
9	9	Yi-tung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:42
-	1	("0000424").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 13:47
-	49798	trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 13:47
-	389	trench and shore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 13:48
-	4	(trench and shore) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 14:29
-	1055	(438/692).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 12:44
-	14	((438/692).CCLS.) and (shore or (shore adj D))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 14:35

	3	((438/692).CCLS.) and (shore or (shore adj D)) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 14:35
	114633	(silicon adj (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 15:34
	127	((silicon adj (substrate or wafer))) and (shore or (shore adj d))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 15:49
	4	((silicon adj (substrate or wafer))) and (shore or (shore adj d)) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 15:49
	1	("20020160546").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:07
	14734	photo adj resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:15
	3895	trench adj fill\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:09
	53493	trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:09
	22142	cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
	23096	planariz\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
	138	(photo adj resist) and (trench adj fill\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
	61	((photo adj resist) and (trench adj fill\$2)) and cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
	47	((photo adj resist) and (trench adj fill\$2)) and cmp ) and planariz\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
	266601	resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:15

	14734	(photo adj resist) and resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/25 13:16
	856	(trench adj fill\$2) and resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/25 13:16
	351	cmp and ((trench adj fill\$2) and resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/25 13:16
	254	(cmp and ((trench adj fill\$2) and resist)) and planariz\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/25 13:17
	2	("5173439"   "5719073").PN.	USPAT	2002/11/25 13:39
	1	6107187.URPN.	USPAT	2002/11/25 13:39
	2969	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.	USPAT; US-PGPUB	2003/11/05 13:53
	200436	resist or (photo near2 resist)	USPAT; US-PGPUB	2003/07/09 13:35
	838	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.) and (resist or (photo near2 resist))	USPAT; US-PGPUB	2003/07/09 13:34
	24655	((resist or (photo near2 resist)) near (layer or film))	USPAT; US-PGPUB	2003/07/09 13:35
	354	((resist or (photo near2 resist)) near (layer or film)) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.)	USPAT; US-PGPUB	2003/07/09 14:46
	1	6117798.URPN.	USPAT	2003/07/09 14:38
	6	("5607880"   "5747381"   "5783482"   "5948700"   "6030706"   "6030892").PN.	USPAT	2003/07/09 14:38
	1373	((438/424) or (438/427) or (438/443)).CCLS.	USPAT; US-PGPUB	2003/07/09 14:46
	23154	(cmp or ((chemical adj mechanical) near2 polish))	USPAT; US-PGPUB	2003/10/23 16:31
	717	((438/424) or (438/427) or (438/443)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB	2003/07/09 14:47
	78	(((438/424) or (438/427) or (438/443)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish)))) and ((resist or (photo near2 resist)) near (layer or film)))	USPAT; US-PGPUB	2003/07/09 15:59
	71742	dish or dishing	USPAT; US-PGPUB	2003/07/09 15:59
	443	(dish or dishing) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.)	USPAT; US-PGPUB	2003/07/09 16:05
	0	6436833.URPN.	USPAT	2003/07/09 16:28
	6	("5173439"   "5721173"   "5880007"   "6001706"   "6048775"   "6107159").PN.	USPAT	2003/07/09 16:28
	4	6171962.URPN.	USPAT	2003/07/09 16:45
	5	("4613888"   "5094972"   "5298110"   "5702977"   "5817567").PN.	USPAT	2003/07/09 16:45
	138	(((438/424) or (438/427) or (438/443)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish)))) and (dish or dishing)	USPAT; US-PGPUB	2003/07/09 16:52
	3875	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/10/23 16:34

	50475	(rie or (reactive near2 ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:30
	32793	(cmp or ((chemical adj mechanical) near2 polish))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:10
	1901	((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:31
	156	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.) and ((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:31
	7962	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:32
	12015	(photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11
	1202	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:48
	129	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))) and ((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:09
	1377	((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:05
	129	((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))) and ((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:05
	4048	((cmp or ((chemical adj mechanical) near2 polish))) same (photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11
	4143	((cmp or ((chemical adj mechanical) near2 polish))) same (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11

	419832	(photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11
	4143	((cmp or ((chemical adj mechanical) near2 polish))) same ((photoresist or resist) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:12
	1296	((cmp or ((chemical adj mechanical) near2 polish))) with ((photoresist or resist) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:12
	451	((((cmp or ((chemical adj mechanical) near2 polish))) with ((photoresist or resist) )) and ((rie or (reactive near2 ion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:12
	55	((((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and (((((cmp or ((chemical adj mechanical) near2 polish))) with ((photoresist or resist) )) and ((rie or (reactive near2 ion)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:15
	624	((((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))) same ((photoresist or resist) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:17
	42	(((((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))) same ((photoresist or resist) )) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:44
	244	((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:37
	28	((((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist) )) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:44
1		("6613690").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/24 11:44
	0	6613690.URPN.	USPAT	2003/10/24 11:44
	8	("4385975"   "5065273"   "5077234"   "5100823"   "5723374"   "5759262"   "6130126"   "6420226").PN.	USPAT	2003/10/24 11:44
	2	6420226.URPN.	USPAT	2003/10/24 11:54
	9	("5468979"   "5805494"   "5972759"   "6013547"   "6080638"   "6130470"   "6150686"   "6174764"   "6340623").PN.	USPAT	2003/10/24 11:54
	7620	((438/780) or (438/781) or (438/782) or (438/692) or (438/626) or (438/631) or (438/633) or (438/693) or (438/725) or (438/697) or (438/699) or (438/760)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:57

	39447	cmp or (chemical adj mechanical adj (polishing or planarizing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:58
	421221	resist or photoresist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:59
	19	((438/780) or (438/781) or (438/782) or (438/692) or (438/626) or (438/631) or (438/633) or (438/693) or (438/725) or (438/697) or (438/699) or (438/760)).CCLS.) and ((cmp or (chemical adj mechanical adj (polishing or planarizing))) near (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:59
	157	(cmp or (chemical adj mechanical adj (polishing or planarizing))) near (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25
	1420928	remove	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25
	8268	remove near (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25
	17	(remove near (resist or photoresist)) with (cmp or (chemical adj mechanical adj (polishing or planarizing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25